



# HEADLINE

## FEATURES:

- 8M x 32 and 2 x 8m x 32 Densities
- Based on Intel's Strataflash (J3) family of Flash Devices
  - E28F640J3
- (64) 128Kb Erase Blocks (Symetrical)
- High Performance Interface Async Page Mode Reads
  - 120/25 ns Read Access Time
- 2.7V -3.6V Vcc Operation
- 128 bit Protection Register;
  - 64 bit Unique Device Identifier
  - 64 bit User Programmable OTP Cells
- Common Flash Interface (CFI)
- Scaleable Command Set (SCS)
- 32 byte Write Buffer, 64M Total Erase Cycles
  - 100,000 Erase Cycles per Block
- Package
  - 80 pin SIMM

## DESCRIPTION:

The WED7F328XDNSN and WED7F2328XDNSN are organized as one and two banks of 8M x 32 respectively. The modules are based on Intel's E28F640J3, 8M x 8 / 4M x 16 device family. Both modules offer access times of 120-150ns.

### PIN CONFIGURATIONS

Pin#	Pin Name	Pin#	Pin Name	Pin#	Pin Name	Pin#	Pin Name
1	V <sub>SS</sub>	21	NC	41	A <sub>11</sub>	61	DQ <sub>9</sub>
2	V <sub>CC</sub>	22	NC	42	A <sub>10</sub>	62	DQ <sub>8</sub>
3	NC	23	*	43	A <sub>9</sub>	63	DQ <sub>7</sub>
4	$\bar{G}$	24	*	44	A <sub>8</sub>	64	DQ <sub>6</sub>
5	$\bar{W}_0$	25	V <sub>SS</sub>	45	A <sub>7</sub>	65	DQ <sub>5</sub>
6	$\bar{W}_1$	26	DQ <sub>29</sub>	46	A <sub>6</sub>	66	DQ <sub>4</sub>
7	NC	27	DQ <sub>30</sub>	47	A <sub>5</sub>	67	DQ <sub>3</sub>
8	DQ <sub>16</sub>	28	DQ <sub>31</sub>	48	A <sub>4</sub>	68	DQ <sub>2</sub>
9	DQ <sub>17</sub>	29	$\bar{W}_2$	49	A <sub>3</sub>	69	DQ <sub>1</sub>
10	DQ <sub>18</sub>	30	NC	50	A <sub>2</sub>	70	DQ <sub>0</sub>
11	DQ <sub>19</sub>	31	A <sub>21</sub>	51	A <sub>1</sub>	71	NC
12	DQ <sub>20</sub>	32	A <sub>20</sub>	52	$\bar{A}_0$	72	V <sub>CC</sub>
13	DQ <sub>21</sub>	33	A <sub>19</sub>	53	$\bar{W}_3$	73	PD <sub>1</sub>
14	DQ <sub>22</sub>	34	A <sub>18</sub>	54	V <sub>SS</sub>	74	PD <sub>2</sub>
15	DQ <sub>23</sub>	35	A <sub>17</sub>	55	DQ <sub>15</sub>	75	PD <sub>3</sub>
16	DQ <sub>24</sub>	36	A <sub>16</sub>	56	DQ <sub>14</sub>	76	PD <sub>4</sub>
17	DQ <sub>25</sub>	37	A <sub>15</sub>	57	DQ <sub>13</sub>	77	PD <sub>5</sub>
18	DQ <sub>26</sub>	38	A <sub>14</sub>	58	DQ <sub>12</sub>	78	PD <sub>6</sub>
19	DQ <sub>27</sub>	39	A <sub>13</sub>	59	DQ <sub>11</sub>	79	PD <sub>7</sub>
20	DQ <sub>28</sub>	40	A <sub>12</sub>	60	DQ <sub>10</sub>	80	V <sub>SS</sub>

### CAPACITANCE

Parameter	Sym	8M x32	2 x 8M x 32	Unit
		Max	Max	
Address Lines	CA	35	70	pF
Data lines	CDQ	15	30	pF
Chip & Write Enable Lines	CG	15	30	pF
Output Enable Lines	CG	35	70	pF

\* SIMM DENSITY

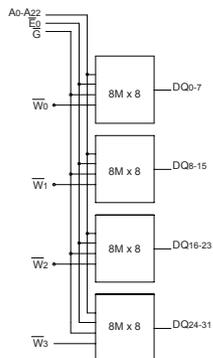
32MB PIN 24=  $\bar{E}_0$  PIN 23= NC

64MB PIN 24=  $E_0$  PIN 23=  $\bar{E}_1$

**FIG. 1**  
**BLOCK DIAGRAMS**

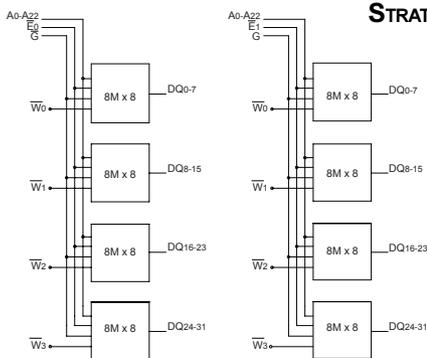
**WED7F328XDNSN: 8M x 32**

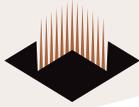
**STRATAFLASH**



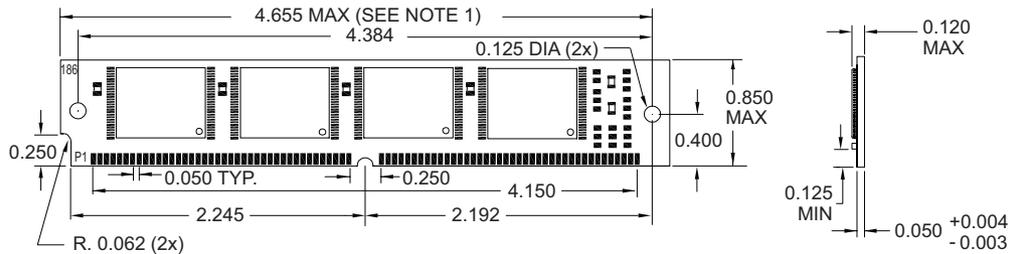
**WED7F2328XDNSN: 2 x 8M x 32**

**STRATAFLASH**



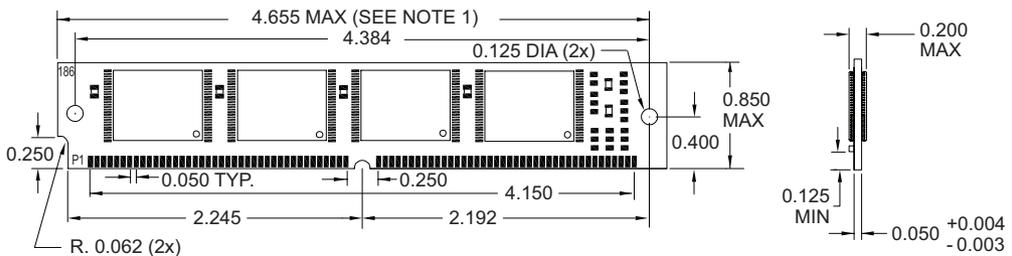


**FIG. 2 MECHANICAL PACKAGE**



NOTE: THE MAXIMUM DIMENSION TO BE MEASURED WITHOUT INCLUDING THE BREAKAWAY AREA.

**FIG. 3 MECHANICAL PACKAGE**



NOTE: THE MAXIMUM DIMENSION TO BE MEASURED WITHOUT INCLUDING THE BREAKAWAY AREA.

**MODULE SPEED VIA PRESENCE DETECT**

Module Speed Identification			
Max Access Time	Presence Select Pin		
	PD5	PD6	PD7
Not Def.	1	1	1
120ns	0	1	0
150ns	1	0	0

**ORDERING INFORMATION**

Part Number	Speed (ns)	Density
WED7F328XDNSN120C	120	32MB
WED7F328XDNSN150C	150	32MB
WED7F2328XDNSN120C	120	64MB
WED7F2328XDNSN150C	150	64MB